

Author: Kunihiro Suzuki Fujitsu limited Japan



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Ion Implantation and Activation Volume 2

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About the ebook

The models described in this volume cover the following topics: two- and three-dimensional profiles in various shapes of the substrates, amorphous layer thickness prediction in wide ion implantation conditions at various ion implantation temperatures, speed of the regrowth of the amorphous layer and the redistribution of the profiles during solid phase epitaxial recrystallization (SPE) and isolated impurities in SPE processes.

Contents

- Ion Implantation Profile in Patterned Substrate
- Analytical Model for Two-Dimensional Profile in MOSFET's
- Three-Dimensional Ion Implantation Profile Based on Rp Line Concept
- Ion Implantation Profile in Multi-Layer Structure
- Dose Loss
- Amorphous Layer Thickness
- Recrystallization of Amorphous Layer
- Redistribution of Impurities During Solid Phase Epitaxy
- Activation of Ion Implanted Impurities

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